

LE 1965473A1

L6 ANSWER 24 OF 98 CAPLUS COPYRIGHT 1999 ACS
 AN 1997:502314 CAPLUS
 DN 127:115293
 TI Semiconductor device and its manufacture
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 PA Kabushiki Kaisha Toshiba, Japan
 SO Ger. Offen., 33 pp.
 CODEN: GWXXBX

DT Patent

LA German

IC ICM H01L021-31

ICS H01L021-469

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other
 Reprographic Processes)
 Section cross-reference(s): 42, 76

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	DE 19654737	A1	19970703		
	JP 09237785	A2	19970909	DE 1996-19654737	19961230
PRAI	JP 1995-342894		19951228	JP 1996-68830	19960325
	JP 1996-68830		19960325		

AB The title device comprises a substrate and at least one
 interlayer-isolation film on one passivation-isolation film, wherein the
 film is formed on the substrate and contains Si, O,
 C and H, where the content of C is not smaller than the content of
 Si. The isolation film may have a dielec. const. of 1.3-3.2. The
 isolation film may comprise -(SiR1R2-O-SiR1R2-O)n- [R1 = CnH2n+1,
 OCnH2n+1; R2 = CnH2n+1, OC2n+1; n, m = d.p.]. The manuf. is carried out
 by a plasma CVD method.

ST semiconductor device isolation film plasma CVD
 IT Polysiloxanes, processes
 RL: DEV (Device component use); PEP (Physical, engineering or chemical
 process); PROC (Process); USES (Uses)
 (isolation film of semiconductor device)

IT Plasma chemical vapor deposition
Semiconductor devices

(semiconductor device and its manuf.)
 IT 75-76-3, Tetramethylsilane 78-10-4, Tetraethoxysilane 631-36-7,
 Tetraethylsilane 681-84-5, Tetramethoxysilane 1450-14-2,
 Hexamethyldisilane 1992-48-9, Tetraisopropoxysilane
 RL: PEP (Physical, engineering or chemical process); TEM (Technical or
 engineered material use); PROC (Process); USES (Uses)
 (isolation film of semiconductor device prepd. from)

IT 124-38-9, Carbon dioxide, reactions 630-08-0, Carbon monoxide,
 reactions 7722-84-1, Hydrogen peroxide, reactions 7732-18-5, Water,
 reactions 7782-44-7, Oxygen, reactions 10024-97-2, Nitrogen oxide
 (N2O), reactions 10028-15-6, Ozone, reactions 10102-43-9, Nitrogen
 monoxide, reactions 10102-44-0, Nitrogen dioxide, reactions
 RL: RCT (Reactant)
 (isolation film of semiconductor device prepd. from)

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